

**Vishay Siliconix** 

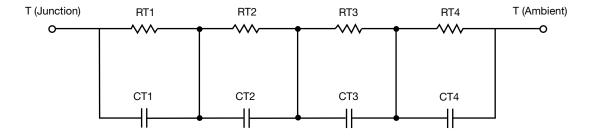
## **R-C Thermal Model Parameters**

#### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

#### **R-C THERMAL MODEL FOR TANK CONFIGURATION**



<b>R-C VALUES FOR TANK</b>	CONFIGURATION		
	THERMAL RES	ISTANCE (°C/W)	
Junction to	Ambient	Case	Foot
RT1	13.1174	342.1165m	N/A
RT2	4.8051	1.2661	N/A
RT3	10.4040	512.7769m	N/A
RT4	56.3139	972.7092m	N/A
	THERMAL CAPAC	ITANCE (Joules/°C)	
Junction to	Ambient	Case	Foot
CT1	231.9471m	53.6330m	N/A
CT2	4.0411m	8.2445m	N/A
CT3	25.5895m	1.4931m	N/A
CT4	1.3188	13.6284m	N/A

Note

• n/a indicates not applicable

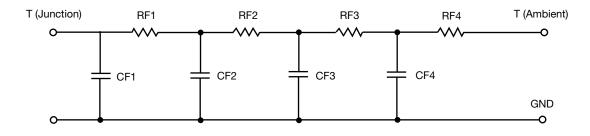
This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.





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### **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RF1	4.6947	706.9061m	N/A		
RF2	14.9779	1.6173	N/A		
RF3	17.0487	754.8991m	N/A		
RF4	48.0392	14.0138m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	2.4283m	953.4192u	N/A		
CF2	19.2484m	3.4377m	N/A		
CF3	311.0537m	4.9362m	N/A		
CF4	1.2225	5.5220u	N/A		

Note

• n/a indicates not applicable



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